

Silicon NPN Power Transistors

2SC2944

DESCRIPTION

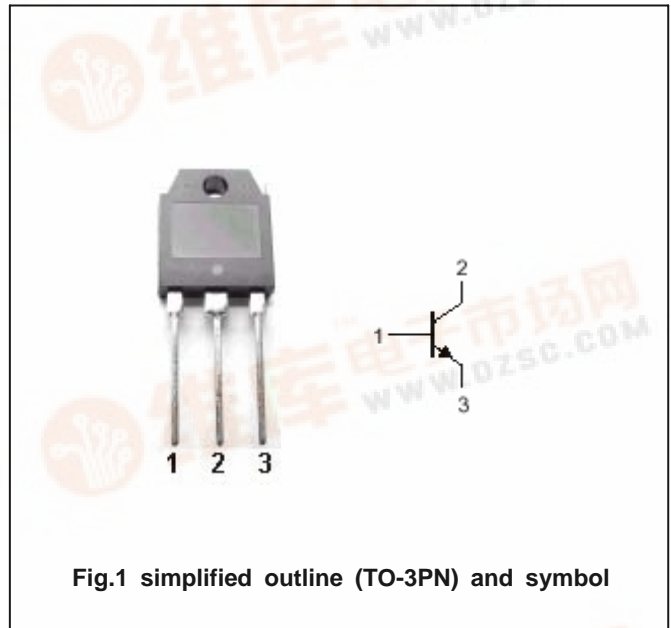
- With TO-3PN package
- High voltage,high speed switching
- High reliability
- Low saturation voltage

APPLICATIONS

- Color & B/W TV power supply
- Active power filter
- Industrial use power supply
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	Open emitter	250	V
V _{CEO}	Collector-emitter voltage	Open base	200	V
V _{EBO}	Emitter-base voltage	Open collector	7	V
I _C	Collector current (DC)		15	A
I _B	Base current (DC)		5	A
P _C	Collector power dissipation	T _C =25°C	100	W
T _j	Junction temperature		150	°C
T _{stg}	Storage temperature		-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal resistance junction case	1.25	°C/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =10mA ; I _B =0	200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =0.1mA ; I _C =0	7			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =0.1mA ; I _E =0	250			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =6A ; I _B =1.2A			0.8	V
V _{BE(sat)}	Base-emitter saturation voltage	I _C =6A ; I _B =1.2A			1.2	V
I _{CBO}	Collector cut-off current	V _{CB} =250V ; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =7V ; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =2A ; V _{CE} =5V	20		80	

Switching times

t _{on}	Turn-on time	I _C =10A ; I _{B1} =-I _{B2} =2A R _L =5 Ω Pw=20 μ s, Duty ≤ 2%			0.8	μ s
t _s	Storage time				1.5	μ s
t _f	Fall time				0.4	μ s

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PACKAGE OUTLINE

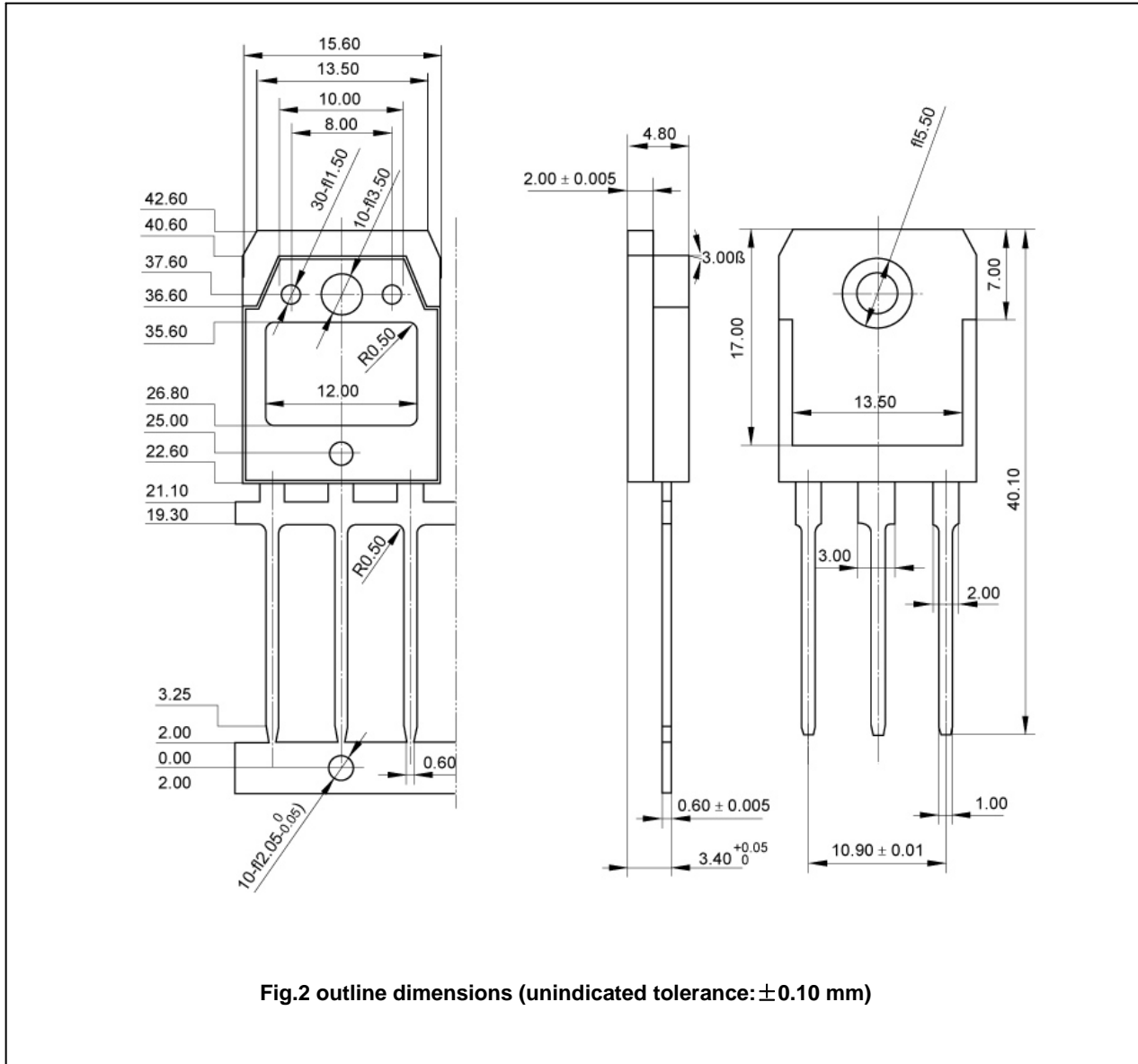


Fig.2 outline dimensions (unindicated tolerance: ±0.10 mm)